

Substitute for form 1449/PTG

APR 26 2006

INFORMATION DISCLOSURE STATEMENT BY APPLICANT

(Use as many sheets as necessary)

Sheet	1	of	2
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Complete if Known

Application Number	10/532,456
Filing Date	04/22/2005
First Named Inventor	GUNTER, Liberty L. et al.
Art Unit	2823
Examiner Name	COLEMAN, William D.
Attorney Docket Number	20030213-US

U. S. PATENT DOCUMENTS

[illegible]

FOREIGN PATENT DOCUMENTS

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Examiner
Signature

/Quovaunda Jefferson/

Date Considered	
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02/25/2008

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NON PATENT LITERATURE DOCUMENTS			
Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published.	T ²
		PCT International Search Report dated April 7, 2005 of International Application No. PCT/US04/32276 filed October 1, 2004.	
		NISHIZAWA, JUN-ICHI et al., "The 2.45 GHz 36 W CW Si Recessed Gate Type SIT with High Gain and High Voltage Operation", IEEE Transactions On Electronic Devices, February 2000, pp. 482-487, Vol. 47, No. 2.	
		HENNING, J.P. et al., "A Novel Self-Aligned Fabrication Process for Microwave Static Induction Transistors in Silicon Carbide", IEEE Electron Device Letters, December 2000, pp. 578-580, Vol. 21, No. 12.	
		BUNEA, GABRIELA E. et al., "Modeling of a GaN Based Static Induction Transistor", Dept. of Physics, Electrical and Computer Engineering, Boston University, pp. 1-6, Boston, MA, (No Date)	
		CAMARCHIA, VITTORIO et al. "Physics-Based Modeling of Submicron GaN Permeable Base Transistors", IEEE Electron Device Letters, June 2002, pp. 303-305, Vol. 23, No. 6.	
		MISRA M. et al. "Investigation of vertical transport in n-GaN films grown by molecular beam epitaxy using Schottky barrier diodes", Applied Physics Letters, Feb. 21, 2000, pp. 1045-1047, Vol. 76, No. 8, American Institute of Physics.	
		BOZLER, CARL O. et al. "Fabrication and Numerical Simulation of the Permeable Base Transistor", IEEE, 1980, pp. 1-14.	

Examiner Signature	/Quovaunda Jefferson/	Date Considered	02/25/2008
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